

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	0	(asymmetric adj area adj memory adj cell) and (colosal adj magnetoresistance adj memory) and CMR	USPAT	OR	ON	2005/03/09 13:12
L2	0	(asymmetric adj area adj memory adj cell) and (colosal adj magnetoresistance) and CMR	USPAT	OR	ON	2005/03/09 13:12
L3	0	asymmetric and (colosal adj magnetoresistance adj memory) and CMR	USPAT	OR	ON	2005/03/09 13:10
L4	0	asymmetric and (colosal adj magnetoresistance) and CMR	USPAT	OR	ON	2005/03/09 13:12
L5	0	(colosal adj magnetoresistance adj memory) and CMR and electrode	USPAT	OR	ON	2005/03/09 13:11
L6	0	(colosal adj magnetoresistance adj memory)and electrode	USPAT	OR	ON	2005/03/09 13:11
L7	0	(asymmetric adj area adj memory adj cell) and (colossal adj magnetoresistance adj memory) and CMR	USPAT	OR	ON	2005/03/09 13:12
L8	0	(asymmetric adj area adj memory adj cell) and (colossal adj magnetoresistance) and CMR	USPAT	OR	ON	2005/03/09 13:12
L9	2	asymmetric and (colossal adj magnetoresistance) and CMR	USPAT	OR	ON	2005/03/09 13:27
L10	2	9 and (memory or electrode or top or bottom or area or asymmetric or CMP or overlying or thickness or etching or etch or side or wall or spacer or insulator or insulating or PCMO or RRAM or HTSC or CMR or metal or interconnect or pulse or plurality or voltage or resistance)	USPAT	OR	ON	2005/03/09 13:30
L11	1	"6353317".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:18
L12	1	"6024885".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:19
L13	1	"5965283".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:19
L14	1	"6261646".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:22
L15	1	"6256222".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:22
L16	1	"6178073".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:23

L17	1	"6023395".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:25
L18	1	"6005753".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:26
L19	1	"5901018".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:26
L20	1	"6023395".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:26
L21	1	"5835003".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:26
L22	0	asymmetric and (colossal adj magnetoresistance adj memory) and CMR and RRAM	USPAT	OR	ON	2005/03/09 13:46
L23	0	asymmetric and (colossal adj magnetoresistance) and CMR and RRAM	USPAT	OR	ON	2005/03/09 13:29
L24	1	("6707122").PN.	USPAT	OR	OFF	2005/03/09 13:29
L25	1	("6480411").PN.	USPAT	OR	OFF	2005/03/09 13:29
L26	1	24 and (memory or electrode or top or bottom or area or asymmetric or CMP or overlying or thickness or etching or etch or side or wall or spacer or insulator or insulating or PCMO or RRAM or HTSC or CMR or metal or interconnect or pulse or plurality or voltage or resistance)	USPAT	OR	ON	2005/03/09 13:31
L27	1	24 and (memory or electrode or top or bottom or area or asymmetric or CMP or overlying or thickness or etching or etch or side or wall or spacer or insulator or insulating or PCMO or RRAM or HTSC or CMR or metal or interconnect or pulse or plurality or voltage or resistance or asymmetric or area or colossal or magnetoresistance)	USPAT	OR	ON	2005/03/09 13:33
L28	1	25 and (memory or electrode or top or bottom or area or asymmetric or CMP or overlying or thickness or etching or etch or side or wall or spacer or insulator or insulating or PCMO or RRAM or HTSC or CMR or metal or interconnect or pulse or plurality or voltage or resistance or asymmetric or area or colossal or magnetoresistance)	USPAT	OR	ON	2005/03/09 13:37
L29	1	("6353317").PN.	USPAT	OR	OFF	2005/03/09 13:37

L30	1	29 and (memory or electrode or top or bottom or area or asymmetric or CMP or overlying or thickness or etching or etch or side or wall or spacer or insulator or insulating or PCMO or RRAM or HTSC or CMR or metal or interconnect or pulse or plurality or voltage or resistance or asymmetric or area or colossal or magnetoresistance)	USPAT	OR	ON	2005/03/09 13:38
L31	1	("5835003").PN.	USPAT	OR	OFF	2005/03/09 13:38
L32	1	31 and (memory or electrode or top or bottom or area or asymmetric or CMP or overlying or thickness or etching or etch or side or wall or spacer or insulator or insulating or PCMO or RRAM or HTSC or CMR or metal or interconnect or pulse or plurality or voltage or resistance or asymmetric or area or colossal or magnetoresistance)	USPAT	OR	ON	2005/03/09 13:44
L33	1	"5508867".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:42
L34	1	"5475550".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:42
L35	1	"5192618".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:43
L36	1	"5181149".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:43
L37	1	"5461308".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:43
L38	1	"5461308".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:43
L39	1	"5432373".PN.	USPAT; USOCR	OR	ON	2005/03/09 13:44
L40	1	("5475550").PN.	USPAT	OR	OFF	2005/03/09 13:44
L41	1	40 and (memory or electrode or top or bottom or area or asymmetric or CMP or overlying or thickness or etching or etch or side or wall or spacer or insulator or insulating or PCMO or RRAM or HTSC or CMR or metal or interconnect or pulse or plurality or voltage or resistance or asymmetric or area or colossal or magnetoresistance)	USPAT	OR	ON	2005/03/09 13:44

L42	0	asymmetric and (colossal adj magnetoresistance adj memory) and electrode and spacer	USPAT	OR	ON	2005/03/09 13:47
L43	0	asymmetric and (colossal adj magnetoresistance) and electrode and spacer	USPAT	OR	ON	2005/03/09 13:48
L44	1	asymmetric and (colossal adj magnetoresistance) and electrode and side and wall	USPAT	OR	ON	2005/03/09 13:50
L45	2162	438/3	USPAT	OR	ON	2005/03/09 13:50
L46	959	438/286	USPAT	OR	ON	2005/03/09 13:50
L47	2272	438/238	USPAT	OR	ON	2005/03/09 13:50
L48	1245	438/381	USPAT	OR	ON	2005/03/09 13:50
L49	3480	438/692	USPAT	OR	ON	2005/03/09 13:51
L50	139	438/927	USPAT	OR	ON	2005/03/09 13:51